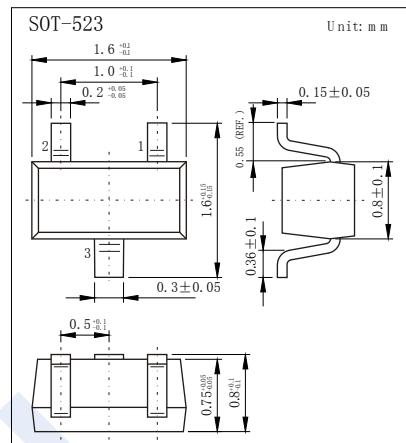
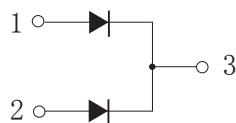


## Switching Diodes

### DAN222 (KAN222)

#### ■ Features

- Four types of packaging are available
- High speed
- Suitable for high packing density layout
- High reliability



#### ■ Absolute Maximum Ratings Ta = 25°C

| Parameter                  | Symbol           | Rating     | Unit |
|----------------------------|------------------|------------|------|
| Peak Reverse Voltage       | V <sub>RM</sub>  | 80         | V    |
| DC Reverse Voltage         | V <sub>R</sub>   | 80         |      |
| Average forward current    | I <sub>o</sub>   | 100        | mA   |
| Peak Forward Surge Current | I <sub>FM</sub>  | 300        |      |
| Power Dissipation          | P <sub>d</sub>   | 150        | mW   |
| Junction Temperature       | T <sub>J</sub>   | 150        | °C   |
| Storage Temperature range  | T <sub>stg</sub> | -55 to 150 |      |

#### ■ Electrical Characteristics Ta = 25°C

| Parameter                       | Symbol          | Test Conditions  | Min | Typ | Max | Unit |
|---------------------------------|-----------------|--|-----|-----|-----|------|
| Reverse breakdown voltage       | V <sub>R</sub>  | I <sub>R</sub> = 100 uA                                  | 80  |     |     | V    |
| Forward voltage                 | V <sub>F</sub>  | I <sub>F</sub> = 100mA                                   |     |     | 1.2 |      |
| Reverse voltage leakage current | I <sub>R</sub>  | V <sub>R</sub> = 70 V                                    |     |     | 0.1 | uA   |
| Junction capacitance            | C <sub>j</sub>  | V <sub>R</sub> = 6 V, f= 1 MHz                           |     |     | 3.5 | pF   |
| Reverse recovery time           | t <sub>rr</sub> | I <sub>F</sub> =I <sub>R</sub> =5mA , V <sub>R</sub> =6V |     |     | 4   | ns   |

#### ■ Marking

|         |   |
|---------|---|
| Marking | N |
|---------|---|

## Switching Diodes

### DAN222 (KAN222)

#### ■ Typical Characteristics

